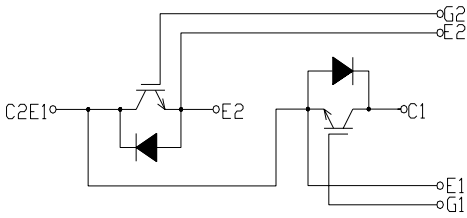
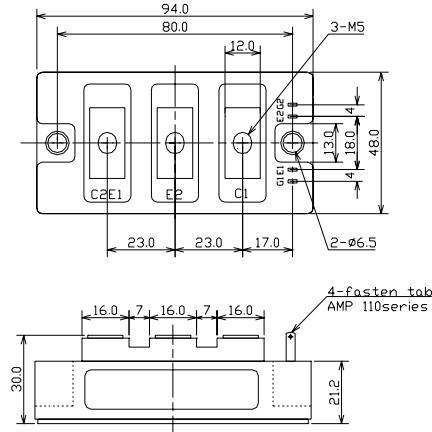


CIRCUIT



OUTLINE DRAWING



4-fasten- tab No 110

Dimension(mm)

Approximate Weight : 320g

MAXMUM RATINGS (Tc=25°C)

| Item | Symbol | PDMB200B12C2 | Unit |
|---|---------------------------|------------------|------|
| Collector-Emitter Voltage | V _{CEs} | 1200 | V |
| Gate - Emitter Voltage | V _{GEs} | +/- 20 | V |
| Collector Current | DC | I _C | 200 |
| | 1 ms | I _C | 400 |
| Collector Power Dissipation | P _C | 960 | W |
| Junction Temperature Range | T _j | -40 to +150 | °C |
| Storage Temperature Range | T _{stg} | -40 to +125 | °C |
| Isolation Voltage (Terminal to Base AC, 1 min.) | V _{ISO} | 2500 | V |
| Mounting Torque | Module Base to Heat sink | F _{TOR} | 2.04 |
| | Bus Bar to Main Terminals | | |
| | | | N•m |

ELECTRICAL CHARACTERISTICS (Tc=25°C)

| Characteristic | Symbol | Test Condition | Min. | Typ. | Max. | Unit | |
|--------------------------------------|----------------------|---|---------------------------|--------|------|------|----|
| Collector-Emitter Cut-Off Current | I _{CEs} | V _{CE} =1200V, V _{GE} =0V | - | - | 4.0 | mA | |
| Gate-Emitter Leakage Current | I _{GES} | V _{GE} =+/- 20V, V _{CE} =0V | - | - | 1.0 | µA | |
| Collector-Emitter Saturation Voltage | V _{CE(sat)} | I _C =200A, V _{GE} =15V | - | 1.9 | 2.4 | V | |
| Gate-Emitter Threshold Voltage | V _{GE(th)} | V _{CE} =5V, I _C =200mA | 4.0 | - | 8.0 | V | |
| Input Capacitance | C _{ies} | V _{CE} =10V, V _{GE} =0V, f=1MHz | - | 16,600 | - | pF | |
| Switching Time | Rise Time | t _r | V _{CC} = 600V | - | 0.25 | 0.45 | µs |
| | Turn-on Time | t _{on} | R _L = 3 ohm | - | 0.40 | 0.7 | |
| | Fall Time | t _f | R _G = 2 ohm | - | 0.25 | 0.35 | |
| | Turn-off Time | t _{off} | V _{GE} = +/- 15V | - | 0.80 | 1.10 | |

FREE WHEELING DIODES RATINGS & CHARACTERISTICS (Tc=25°C)

| Item | Symbol | Rated Value | Unit |
|-----------------|--------|-----------------|------|
| Forward Current | DC | I _F | 200 |
| | 1 ms | I _{FM} | 400 |
| | | | A |

| Characteristic | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|-----------------------|-----------------|--|------|------|------|------|
| Peak Forward Voltage | V _F | I _F =200A, V _{GE} =0V | - | 1.9 | 2.4 | V |
| Reverse Recovery Time | t _{rr} | I _F =200A, V _{GE} =-10V, di/dt=400A/µs | - | 0.2 | 0.3 | µs |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|-------------------|--------|---------------------------------------|------|------|-------|------|
| Thermal Impedance | IGBT | R _{th(j-c)} Junction to Case | - | - | 0.125 | °C/W |
| | DIODE | | - | - | 0.24 | |

Fig.1- Output Characteristics (Typical)

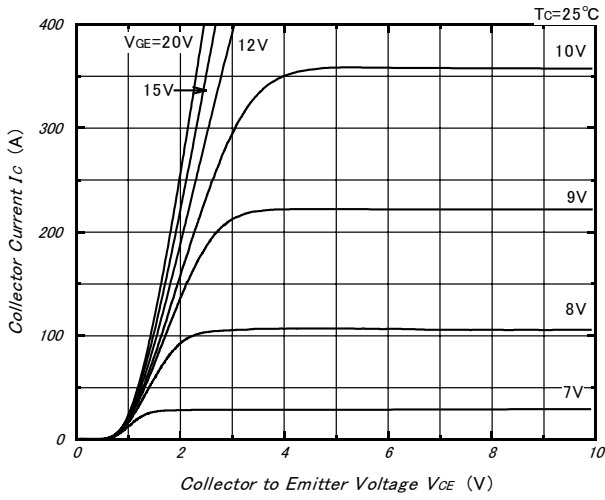


Fig.2- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

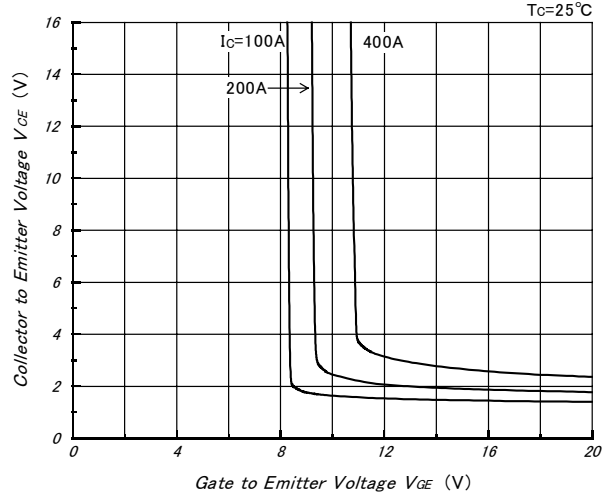


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

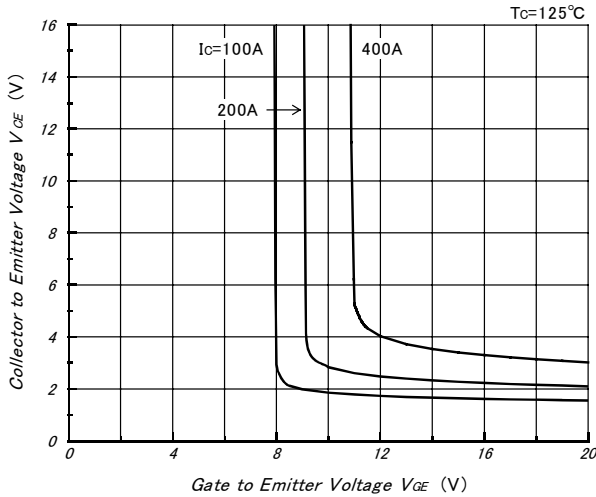


Fig.4- Gate Charge vs. Collector to Emitter Voltage (Typical)

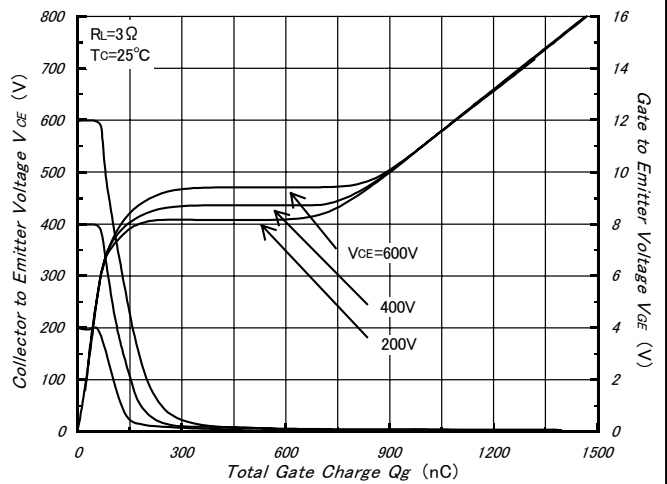


Fig.5- Capacitance vs. Collector to Emitter Voltage (Typical)

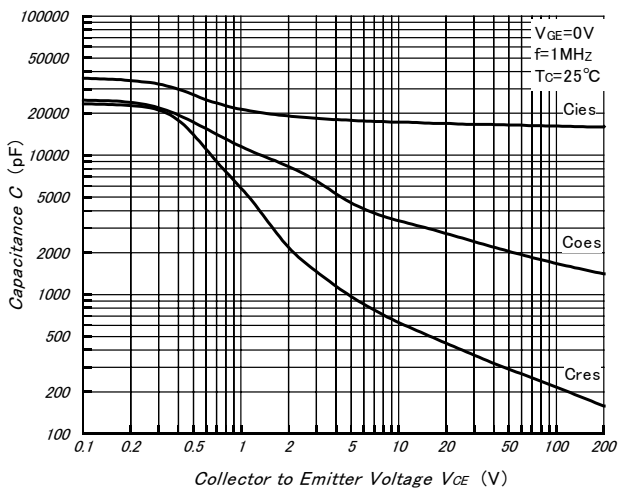


Fig.6- Collector Current vs. Switching Time (Typical)

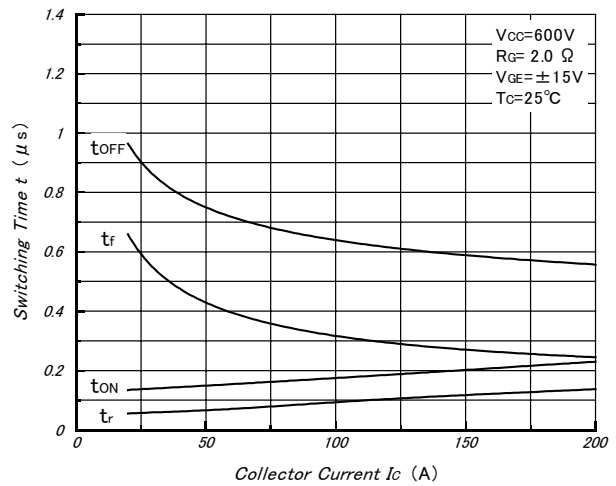


Fig.7- Series Gate Impedance vs. Switching Time (Typical)

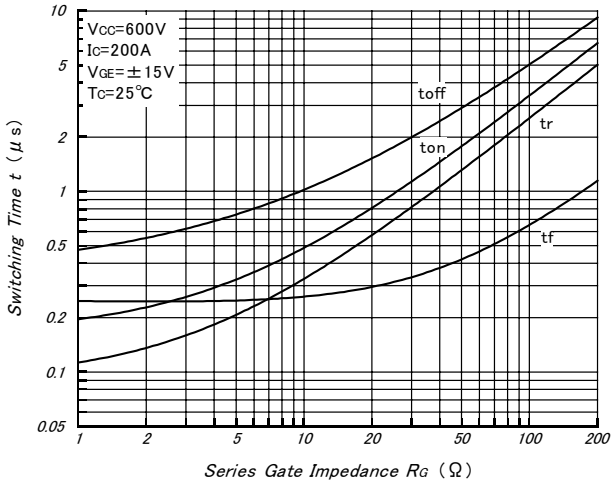


Fig.8- Forward Characteristics of Free Wheeling Diode (Typical)

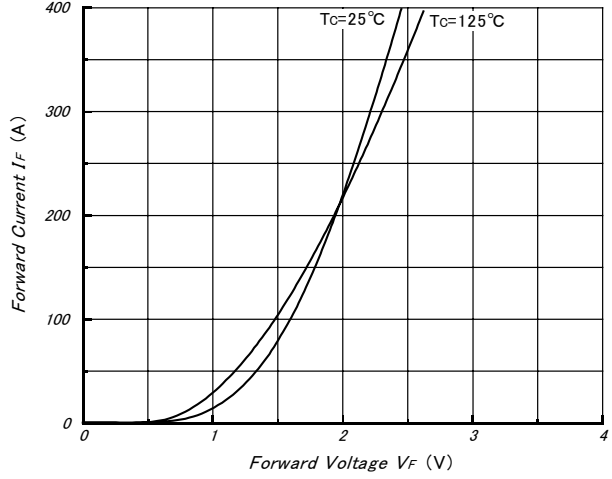


Fig.9- Reverse Recovery Characteristics (Typical)

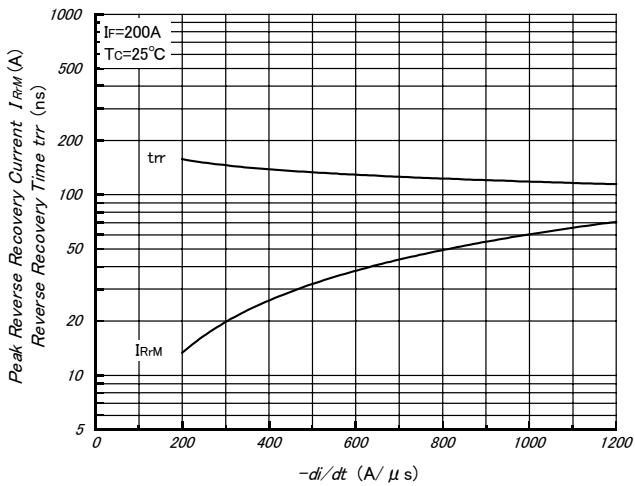


Fig.10- Reverse Bias Safe Operating Area

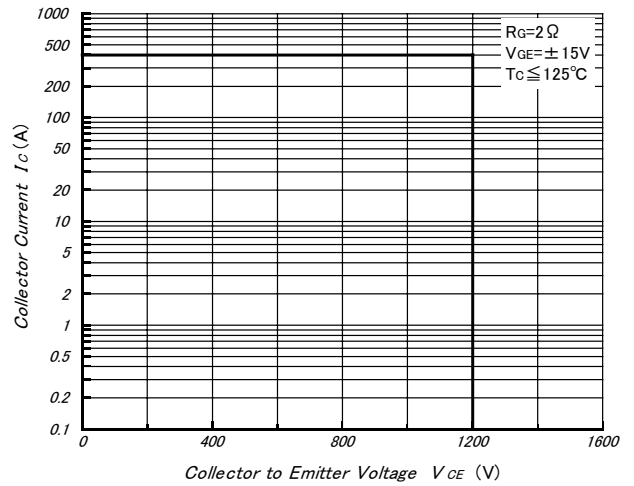


Fig.11- Transient Thermal Impedance

